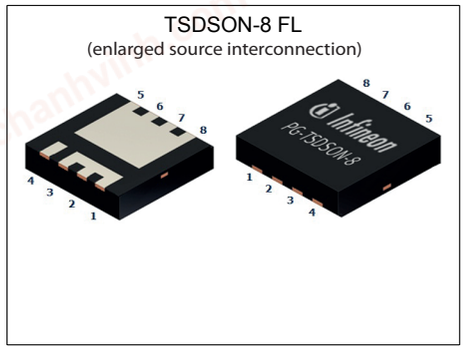
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MOSFET

OptiMOS™5 Power-Transistor, 100 V



Features

- Ideal for high-frequency switching
- Optimized for chargers
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- N-channel, Logic level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Qualified for Standard Grade applications

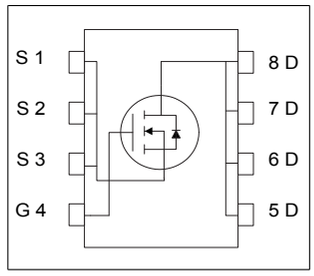


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	14.6	mΩ
I_D	40	A
Q_{OSS}	20	nC
Q_G(0V..4.5V)	8	nC

Type / Ordering Code	Package	Marking	Related Links
BSZ0803LS	PG-TSDSON-8 FL	0803LS	-

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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- - -	- - -	40 28 9	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=10 V, T_A=25 °C, R_{thJA}=60 K/W[1]
Pulsed drain current[2]	$I_{D,pulse}$	-	-	160	A	T_C=25 °C
Avalanche energy, single pulse[3]	E_{AS}	-	-	30	mJ	I_D=20 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	52 2.1	W	T_C=25 °C T_A=25 °C, R_{thJA}=60 K/W[1]
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	1.4	2.4	K/W	-
Device on PCB, minimal footprint	R_{thJA}	-	-	62	K/W	-
Device on PCB, 6 cm^2 cooling area[1]	R_{thJA}	-	-	60	K/W	-

[1] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[2] See Diagram 3 for more detailed information
[3] See Diagram 13 for more detailed information

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3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	1.1	1.7	2.3	V	V_{DS}=V_{GS}, I_D=23 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	16.0 12.4	20.8 14.6	mΩ	V_{GS}=4.5 V, I_D=10 A V_{GS}=10 V, I_D=20 A
Gate resistance[1)]	R_G	-	1	1.5	Ω	-
Transconductance	g_{fs}	18	36	-	S	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=20 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	1000	1300	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	170	220	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	9	15	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	4.7	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=3 Ω
Rise time	t_r	-	3.2	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=3 Ω
Turn-off delay time	$t_{d(off)}$	-	14.3	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=3 Ω
Fall time	t_f	-	3.2	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=20 A, $R_{G,ext}$=3 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	3.2	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge at threshold	$Q_{g(th)}$	-	1.6	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate to drain charge[1)]	Q_{gd}	-	2.8	4.1	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Switching charge	Q_{sw}	-	4.4	-	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	7.6	9.5	nC	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate plateau voltage	$V_{plateau}$	-	3.2	-	V	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge total	Q_g	-	15	-	-	V_{DD}=50 V, I_D=20 A, V_{GS}=0 to 10 V
Output charge[1)]	Q_{oss}	-	20	27	nC	V_{DD}=50 V, V_{GS}=0 V

[1)] Defined by design. Not subject to production test
[2)] See ″Gate charge waveforms″ for parameter definition

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Table 7 Reverse diode

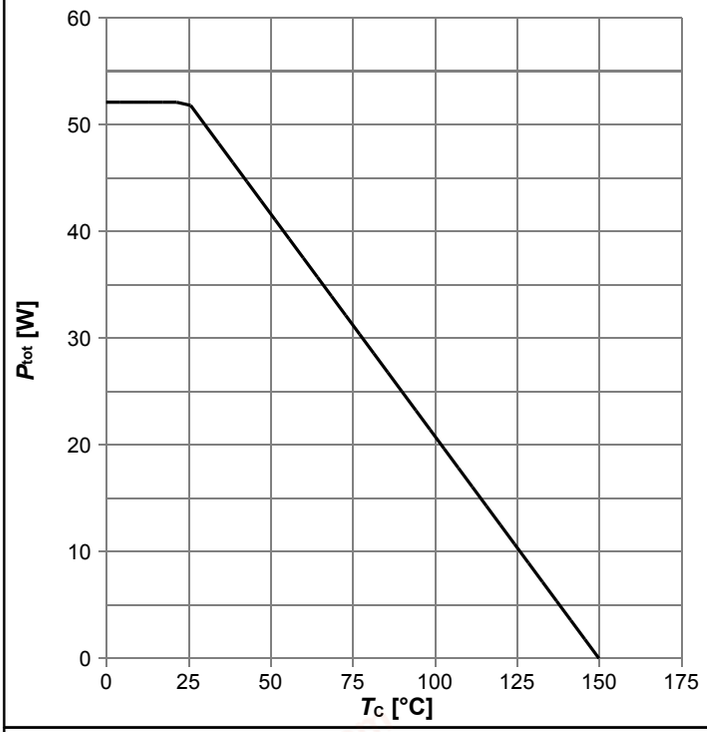
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	40	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	160	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.88	1.1	V	V_{GS}=0 V, I_F=20 A, T_j=25 °C
Reverse recovery time[1)]	t_{rr}	-	26	52	ns	V_R=50 V, I_F=20 A, di_F/dt=100 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	19	38	nC	V_R=50 V, I_F=20 A, di_F/dt=100 A/µs

[1)] Defined by design. Not subject to production test

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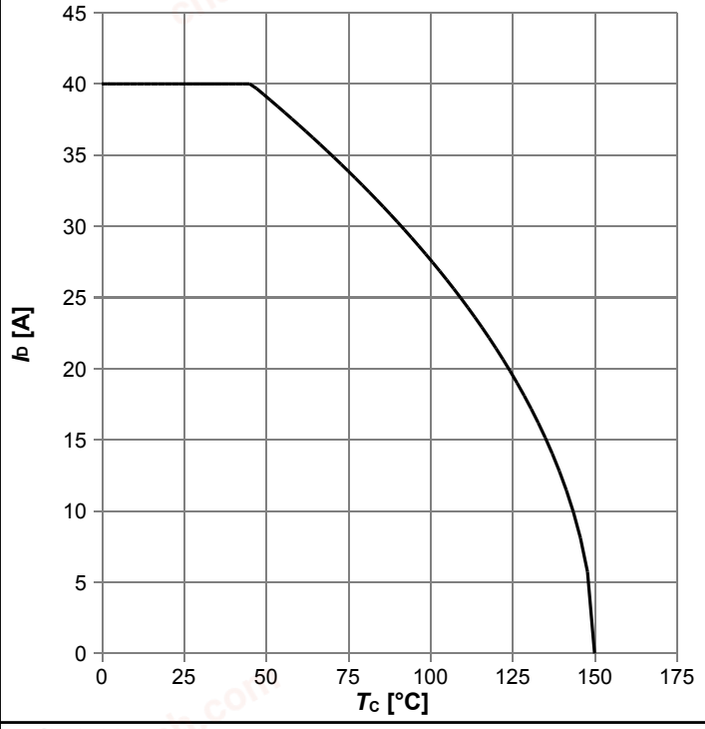
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



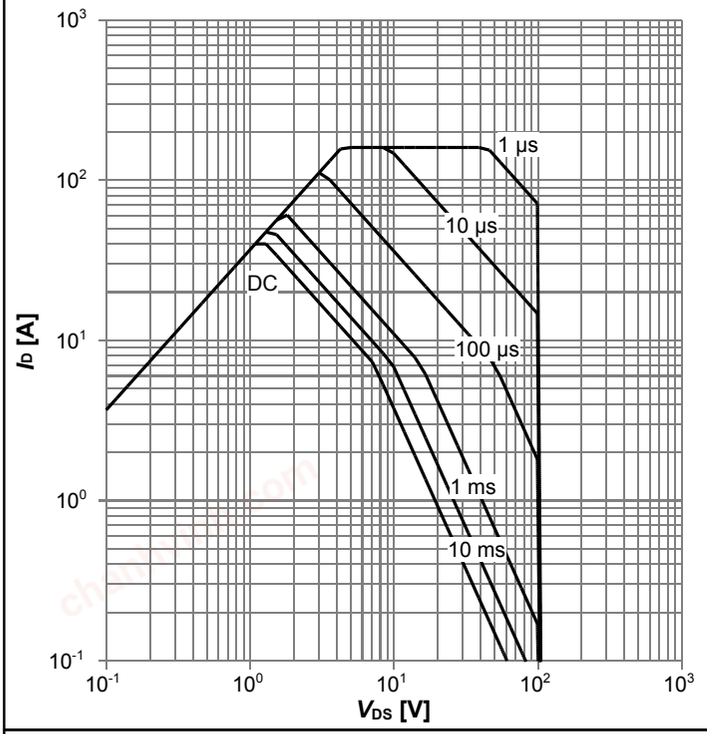
$P_{tot}=f(T_C)$

Diagram 2: Drain current



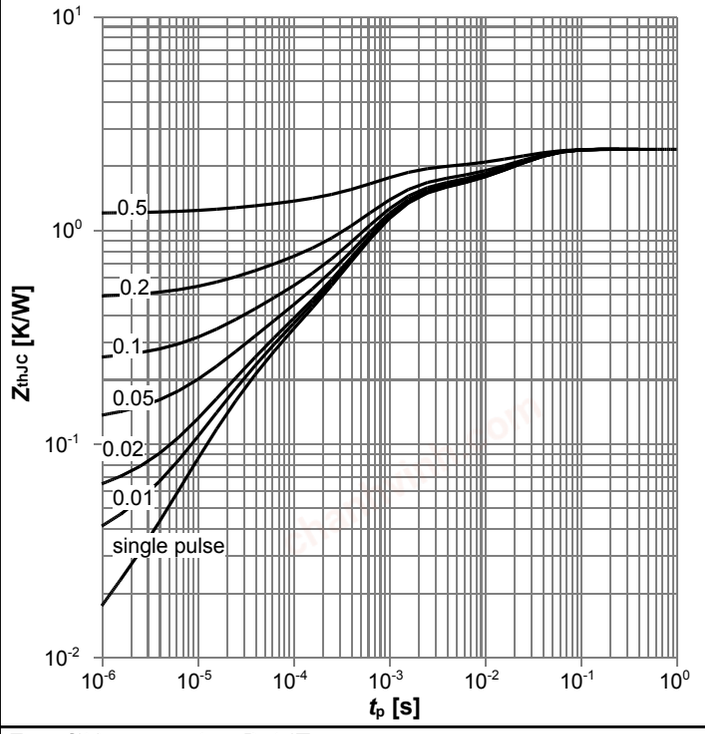
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

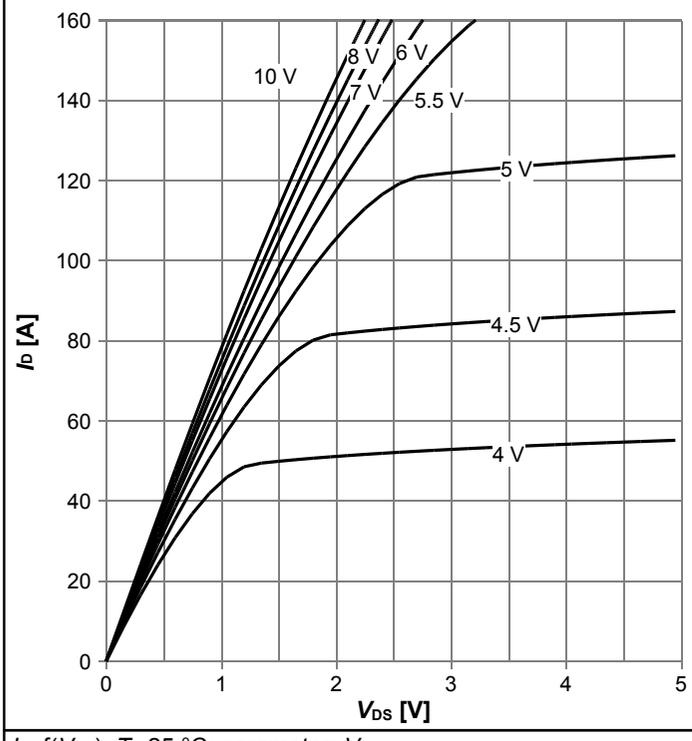
Diagram 4: Max. transient thermal impedance



$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

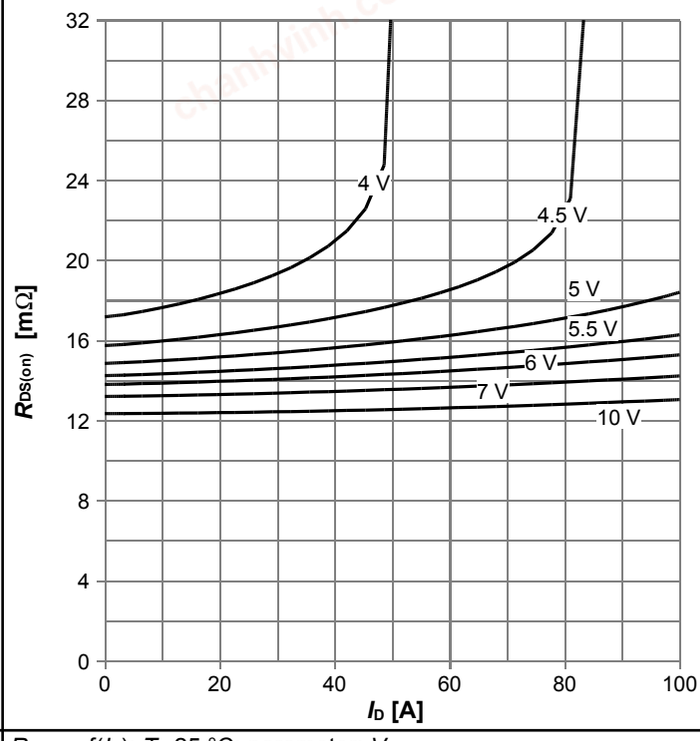
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Diagram 5: Typ. output characteristics



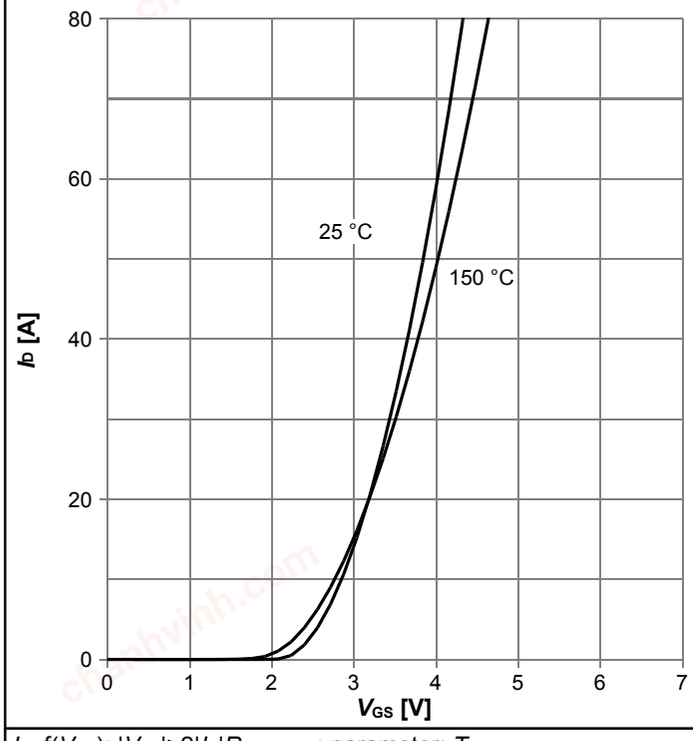
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



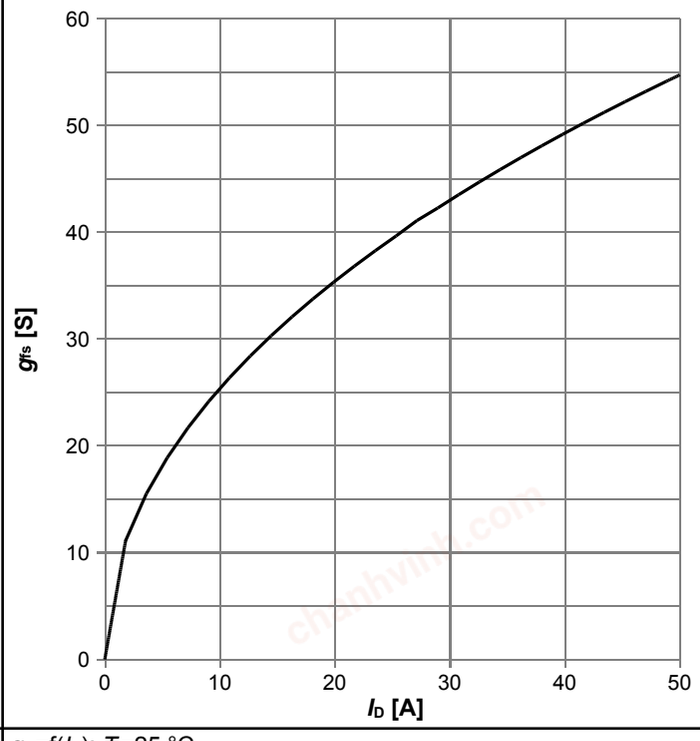
$R_{DS(on)}$=f(I_D); T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

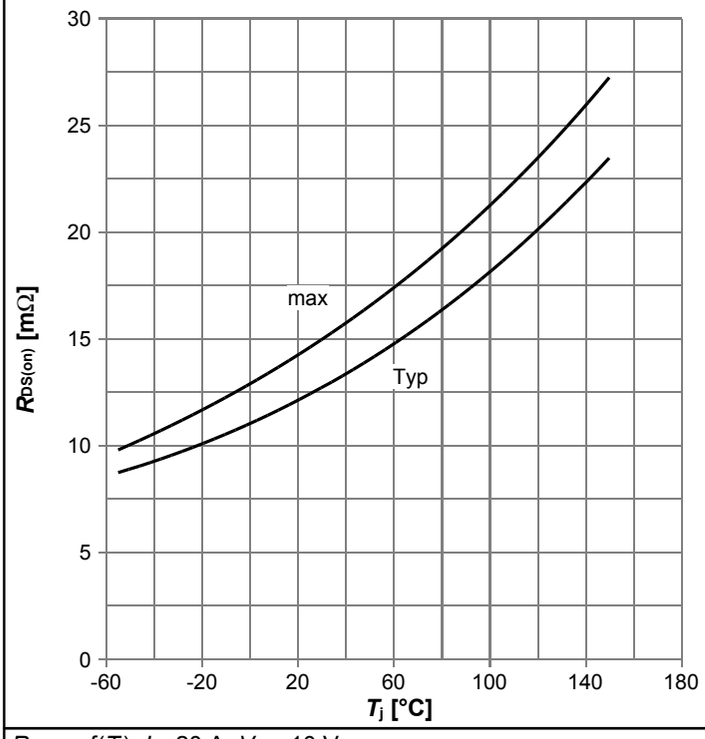
Diagram 8: Typ. forward transconductance



g_{fs}=f(I_D); T_j=25 °C

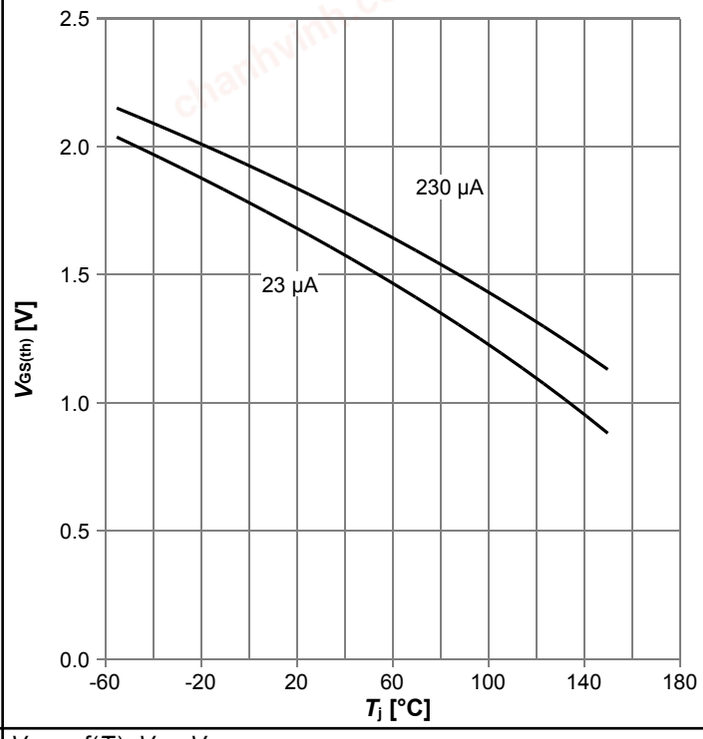
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Diagram 9: Drain-source on-state resistance



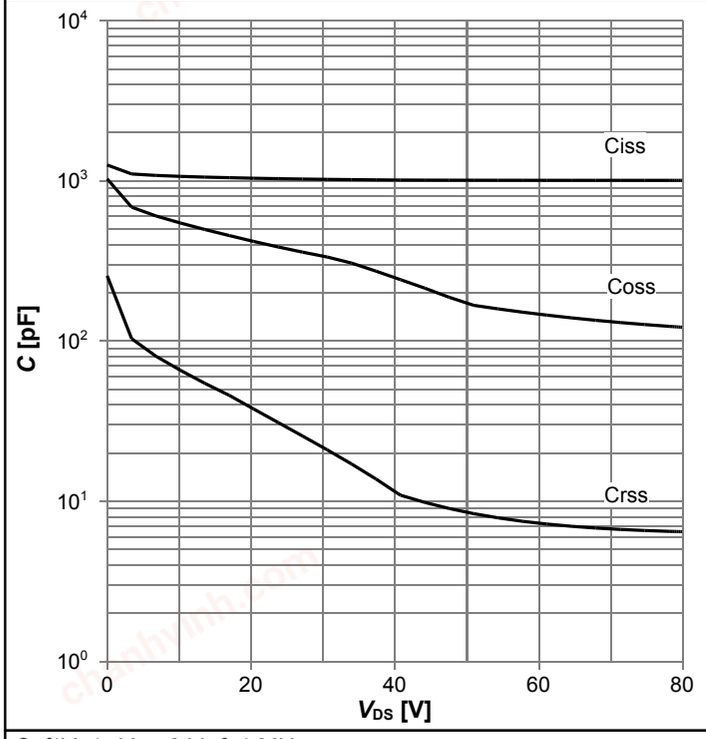
$R_{DS(on)}$=f(T_j); I_D=20 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



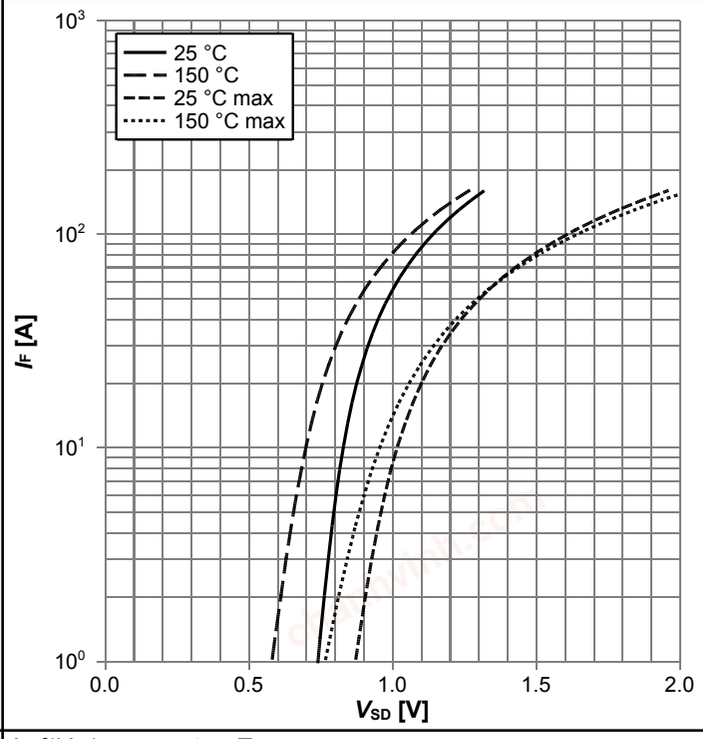
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

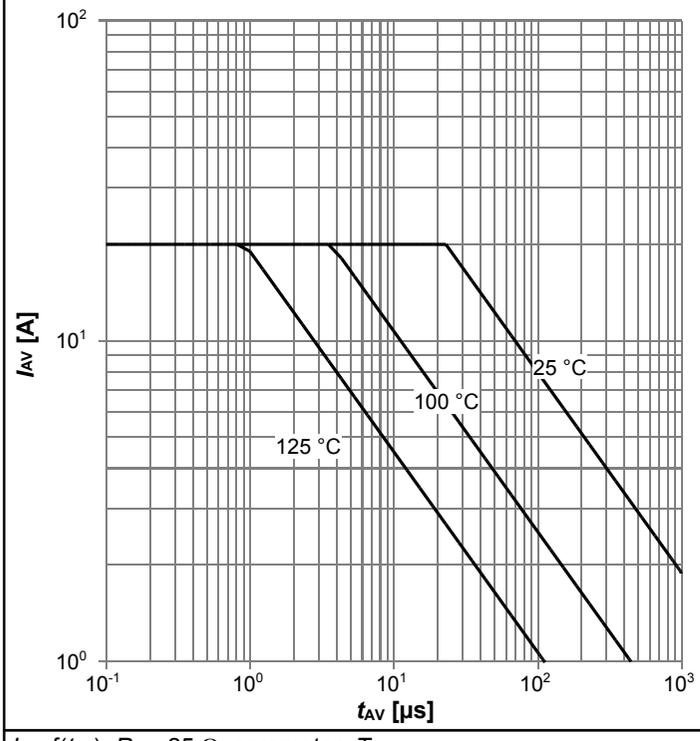
Diagram 12: Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

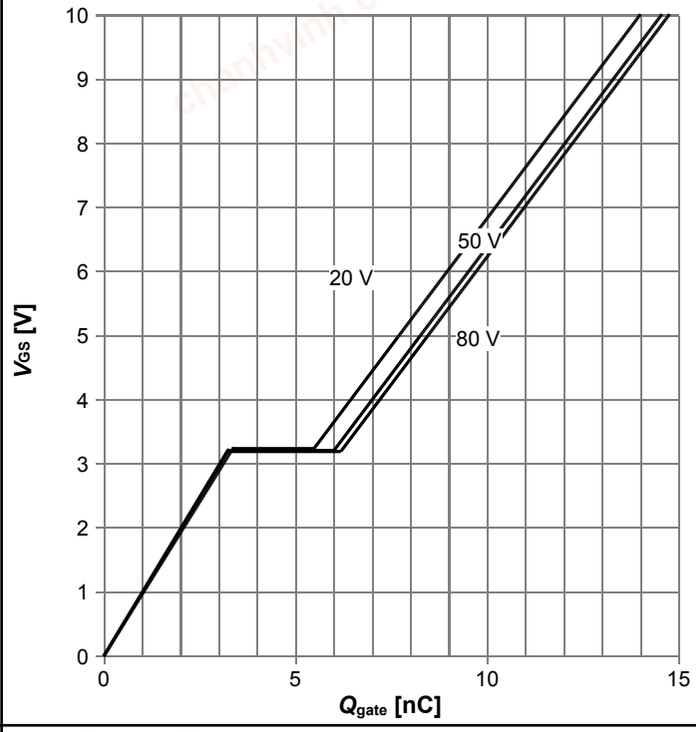
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Diagram 13: Avalanche characteristics



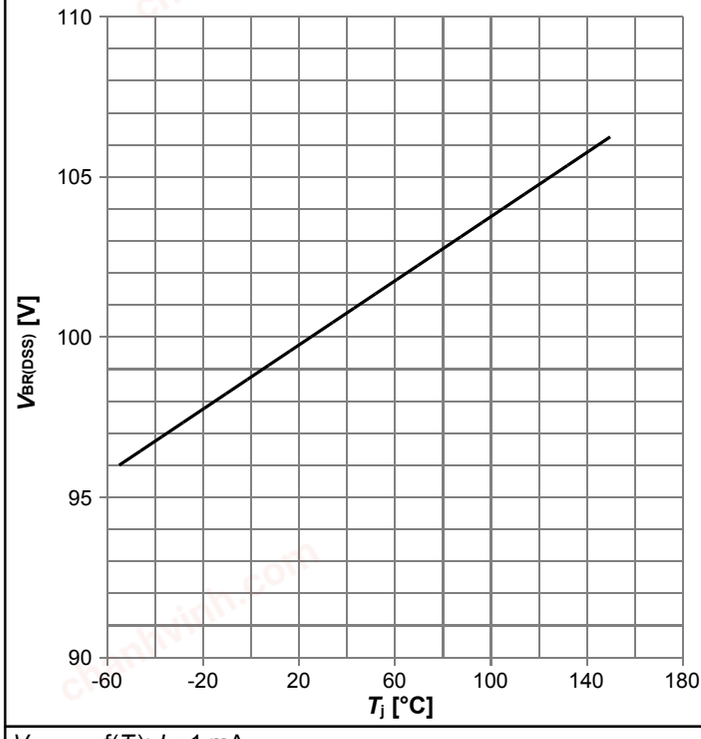
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



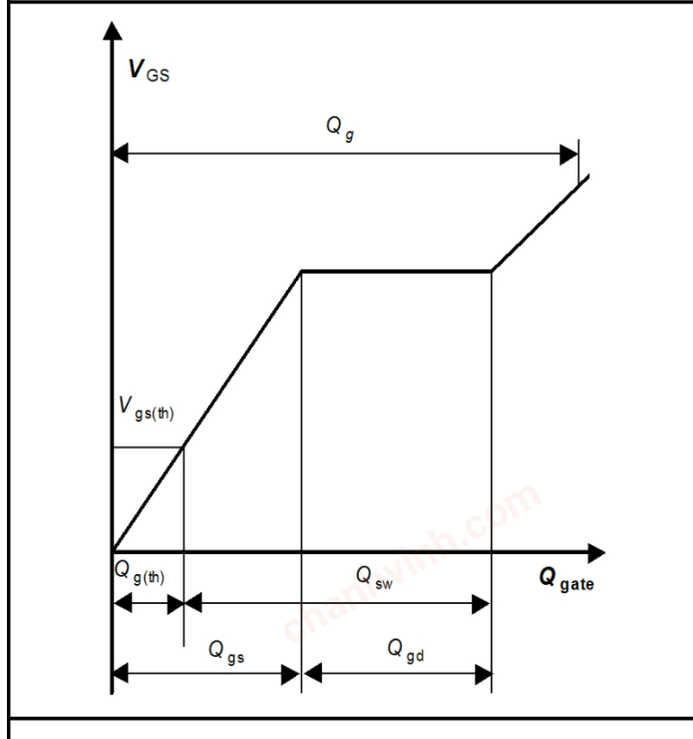
V_{GS}=f(Q_{gate}); I_D=20 A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



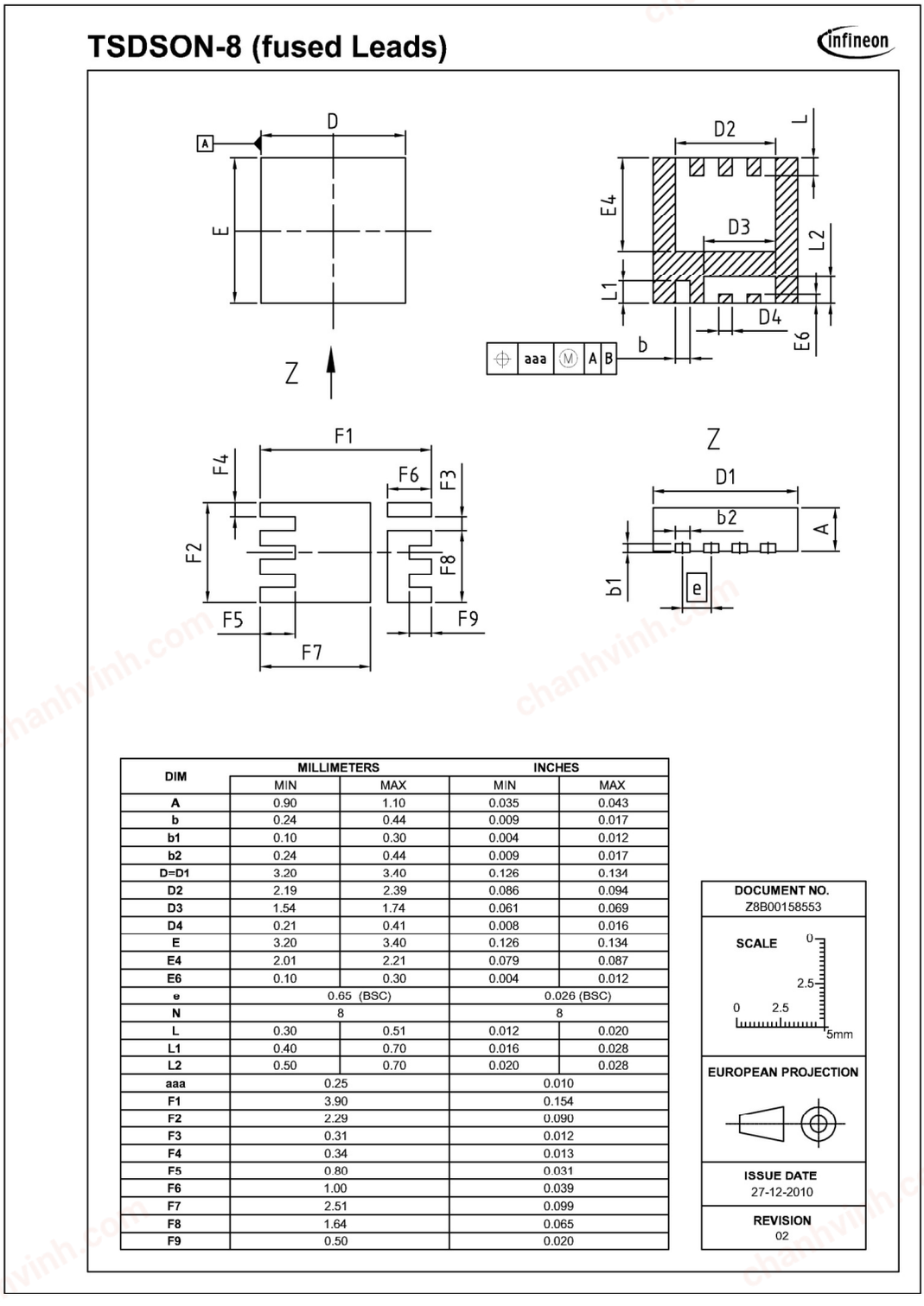
$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Gate charge waveforms



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5 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.24	0.44	0.009	0.017
b1	0.10	0.30	0.004	0.012
b2	0.24	0.44	0.009	0.017
D=D1	3.20	3.40	0.126	0.134
D2	2.19	2.39	0.086	0.094
D3	1.54	1.74	0.061	0.069
D4	0.21	0.41	0.008	0.016
E	3.20	3.40	0.126	0.134
E4	2.01	2.21	0.079	0.087
E6	0.10	0.30	0.004	0.012
e	0.65 (BSC)		0.026 (BSC)	
N	8		8	
L	0.30	0.51	0.012	0.020
L1	0.40	0.70	0.016	0.028
L2	0.50	0.70	0.020	0.028
aaa	0.25		0.010	
F1	3.90		0.154	
F2	2.29		0.090	
F3	0.31		0.012	
F4	0.34		0.013	
F5	0.80		0.031	
F6	1.00		0.039	
F7	2.51		0.099	
F8	1.64		0.065	
F9	0.50		0.020	

DOCUMENT NO.
Z8B00158553

SCALE
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
27-12-2010

REVISION
02

Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

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Revision History

BSZ0803LS

Revision: 2016-10-25, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-08-10	Release of final version
2.1	2016-10-25	Update " Features "

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